

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

The present disclosure provides a technique capable of controlling a decomposition rate of a process gas supplied to a substrate. The technique includes (a) processing a substrate disposed in a process space by controlling a decomposition rate of a process gas supplied into the process space based on a predetermined relationship between the decomposition rate and a residence time of the process gas.

Fig. 7